

Supporting Information

Integration of highly anisotropic multiferroic BaTiO₃-Fe nanocomposite thin films on Si towards device applications

Matias Kalaswad,¹ Bruce Zhang,¹ Xuejing Wang,² Han Wang,² Xingyao Gao,² and Haiyan Wang^{1,2,*}

¹School of Electrical and Computer Engineering, Purdue University, West Lafayette, Indiana 47907, USA

²School of Materials Engineering, Purdue University, West Lafayette, Indiana 47907, USA

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*Author to whom correspondence should be addressed: hwang00@purdue.edu

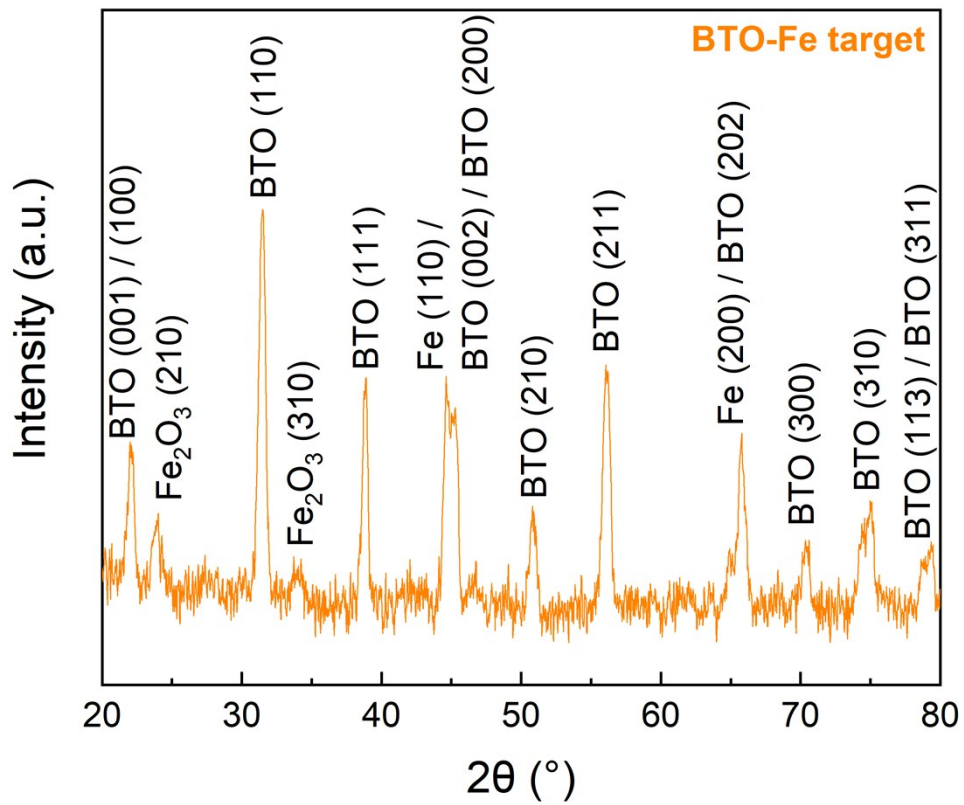


Figure S1. XRD θ - 2θ pattern of the BTO-Fe target showing polycrystalline BTO, Fe, and Fe₂O₃ phases.

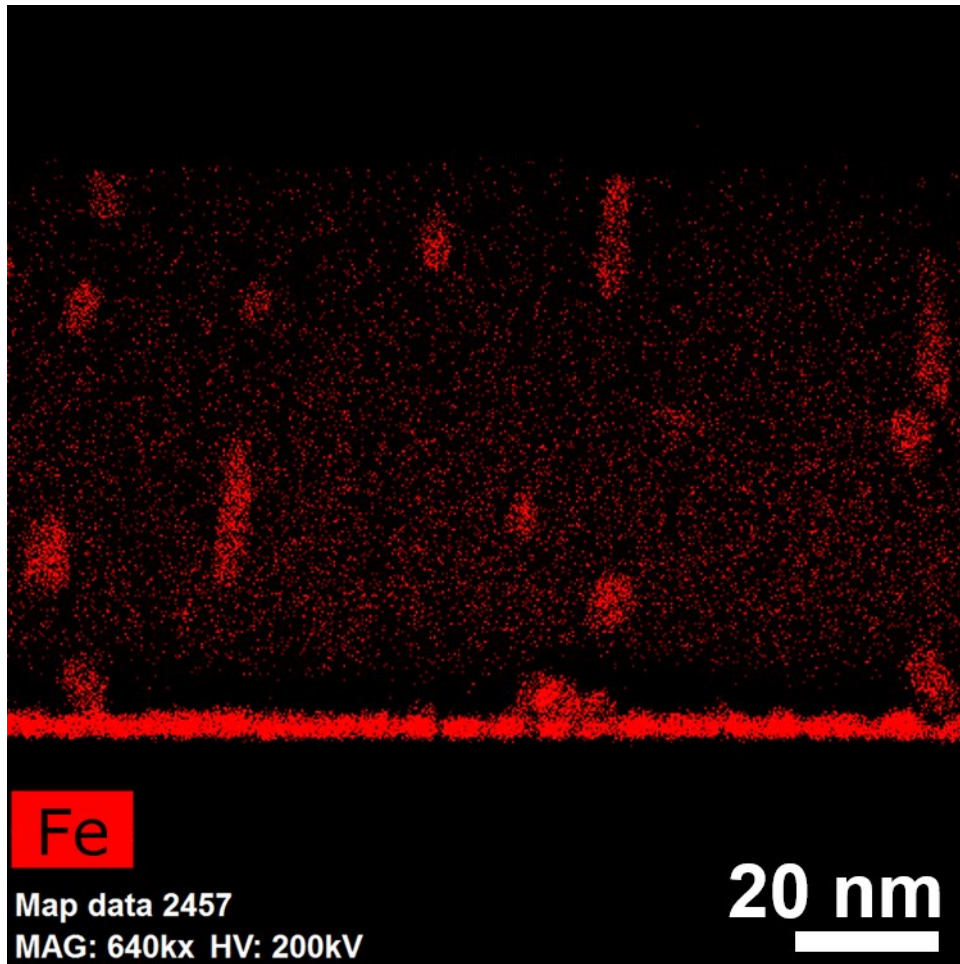


Figure S2. EDS elemental map of the BTO-Fe film grown directly on the Si (001) substrate, without buffer layer.

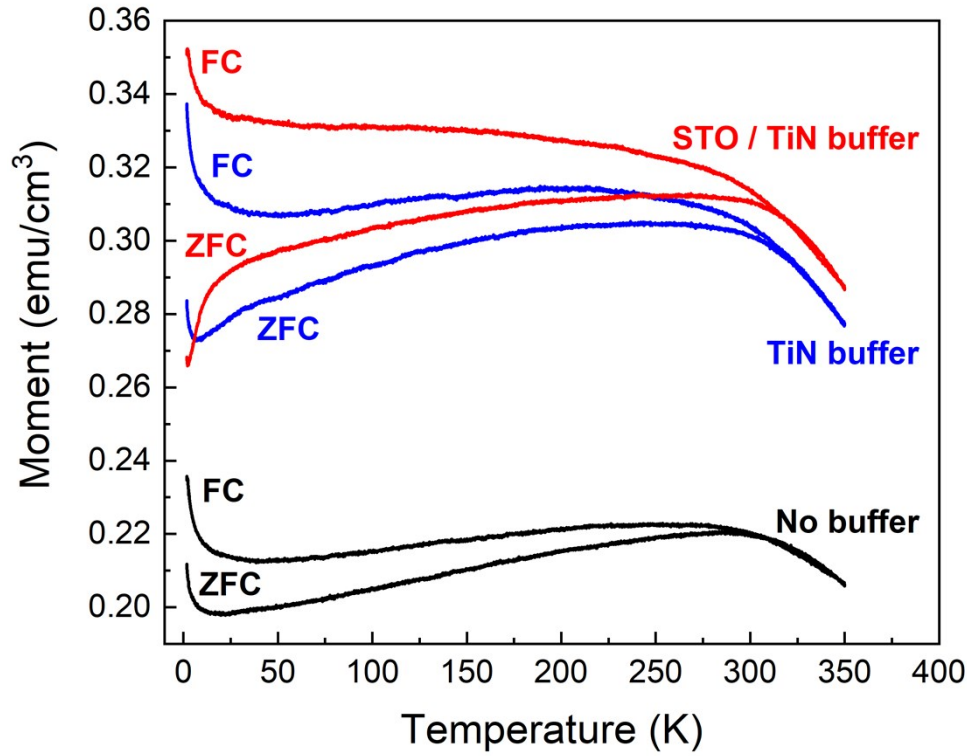


Figure S3. Field cooling (FC) and zero-field cooling (ZFC) M - T curves of the BTO-Fe thin films grown on various buffer layer configurations.

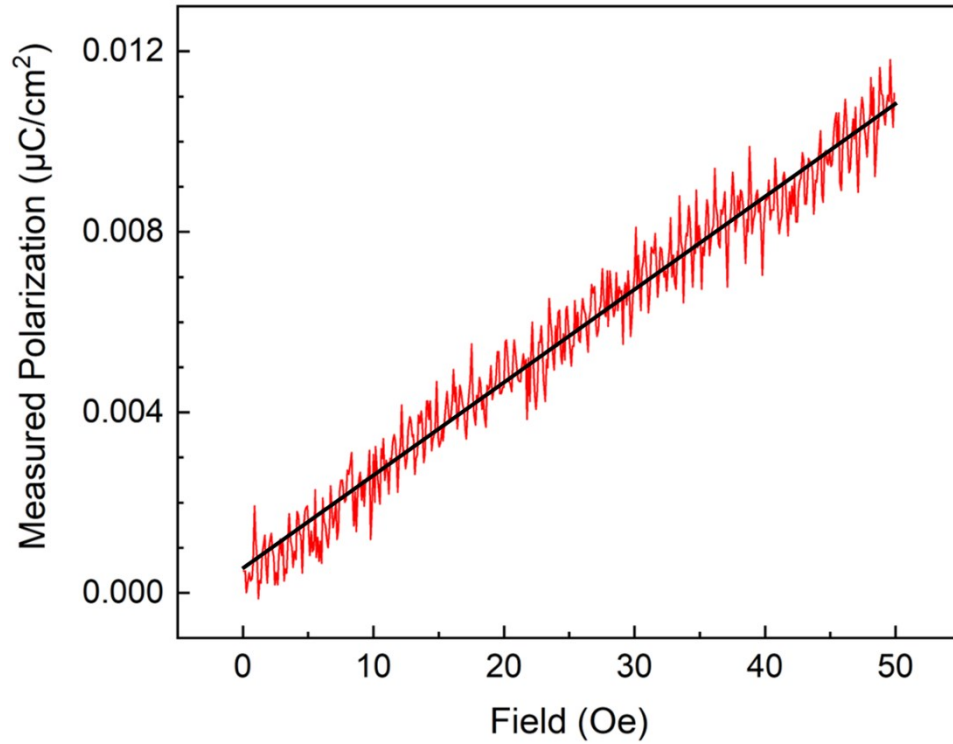


Figure S4. Room-temperature polarization as a function of magnetic field of the BTO-Fe nanocomposite thin film grown on a bilayer-buffered (STO / TiN) silicon substrate. The black line represents a linear fit of the data.